

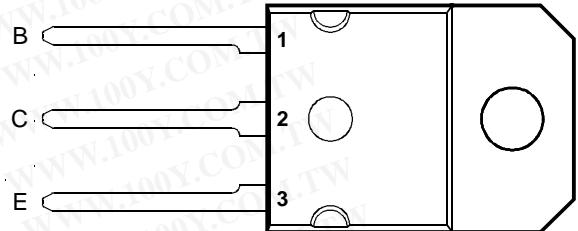
TIP140, TIP141, TIP142 NPN SILICON POWER DARLINGTONS

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DECEMBER 1971 - REVISED MARCH 1997

- Designed for Complementary Use with TIP145, TIP146 and TIP147
- 125 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- Minimum h_{FE} of 1000 at 4 V, 5 A

SOT-93 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRA4

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP140	V_{CBO}	60	V
	TIP141		80	
	TIP142		100	
Collector-emitter voltage ($I_B = 0$)	TIP140	V_{CEO}	60	V
	TIP141		80	
	TIP142		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	10	A
Peak collector current (see Note 1)		I_{CM}	15	A
Continuous base current		I_B	0.5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	125	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	100	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.
3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 5$ mA, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

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PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.

Power
INNOVATIONS

TIP140, TIP141, TIP142

NPN SILICON POWER DARLINGTONS

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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ (see Note 5) $I_B = 0$	TIP140 60 TIP141 80 TIP142 100			V
I_{CEO} Collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$ $I_B = 0$ $V_{CE} = 40 \text{ V}$ $I_B = 0$ $V_{CE} = 50 \text{ V}$ $I_B = 0$	TIP140 TIP141 TIP142		2 2 2	mA
I_{CBO} Collector cut-off current	$V_{CB} = 60 \text{ V}$ $I_E = 0$ $V_{CB} = 80 \text{ V}$ $I_E = 0$ $V_{CB} = 100 \text{ V}$ $I_E = 0$	TIP140 TIP141 TIP142		1 1 1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$ $I_C = 0$			2	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $I_C = 5 \text{ A}$ $V_{CE} = 4 \text{ V}$ $I_C = 10 \text{ A}$	1000 500	(see Notes 5 and 6)		
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 10 \text{ mA}$ $I_C = 5 \text{ A}$ $I_B = 40 \text{ mA}$ $I_C = 10 \text{ A}$	(see Notes 5 and 6)		2 3	V
V_{BE} Base-emitter voltage	$V_{CE} = 4 \text{ V}$ $I_C = 10 \text{ A}$	(see Notes 5 and 6)		3	V
V_{EC} Parallel diode forward voltage	$I_E = 10 \text{ A}$ $I_B = 0$	(see Notes 5 and 6)		3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †	MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = 10 \text{ A}$ $I_{B(on)} = 40 \text{ mA}$ $I_{B(off)} = -40 \text{ mA}$		0.9		μs
t_{off} Turn-off time	$V_{BE(off)} = -4.2 \text{ V}$ $R_L = 3 \Omega$ $t_p = 20 \mu\text{s}$, dc $\leq 2\%$		11		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

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TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
VS
COLLECTOR CURRENT

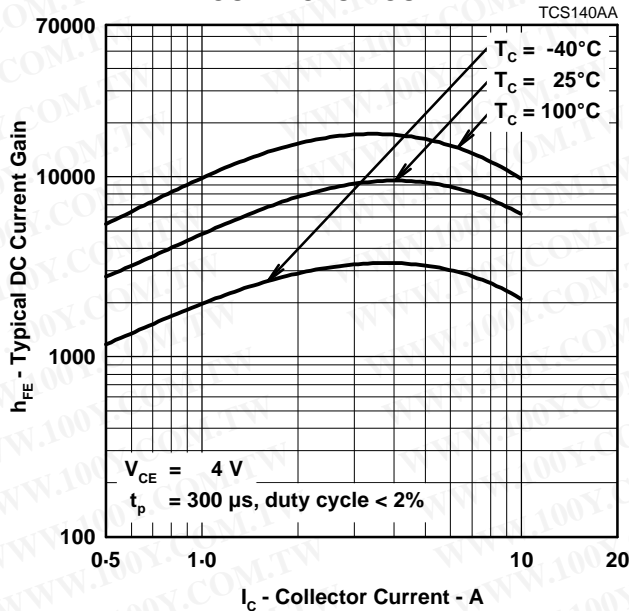


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
VS
COLLECTOR CURRENT

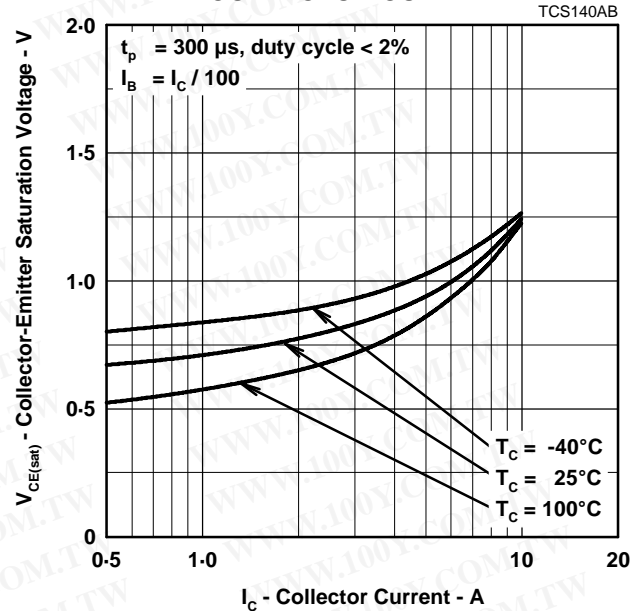


Figure 2.

BASE-EMITTER SATURATION VOLTAGE
VS
COLLECTOR CURRENT

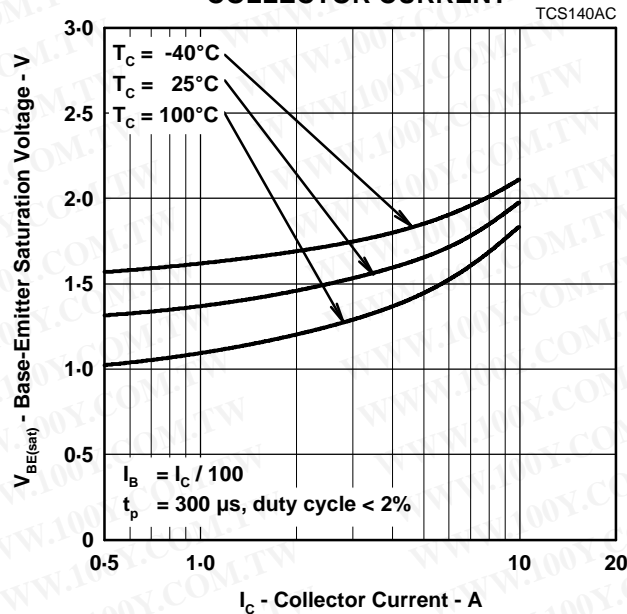


Figure 3.

TIP140, TIP141, TIP142 NPN SILICON POWER DARLINGTONS

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MAXIMUM SAFE OPERATING REGIONS

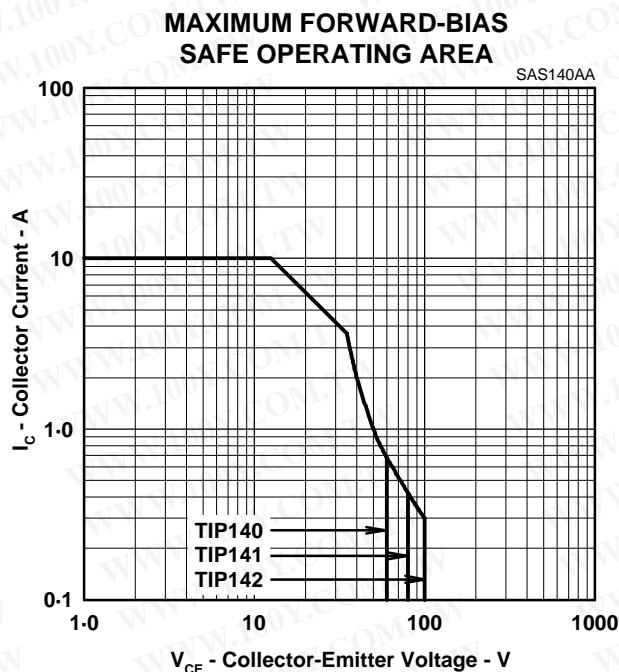


Figure 4.

THERMAL INFORMATION

MAXIMUM POWER DISSIPATION vs CASE TEMPERATURE

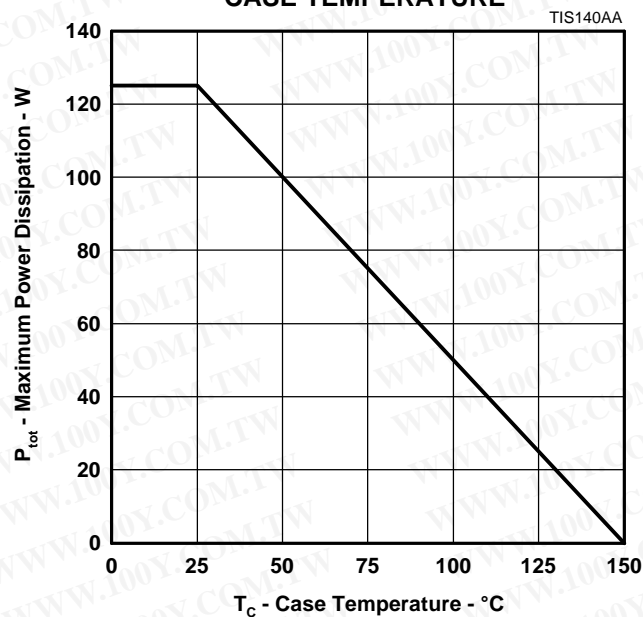


Figure 5.

PRODUCT INFORMATION

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SOT-93

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



MDXXAW

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